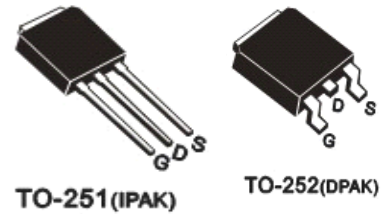
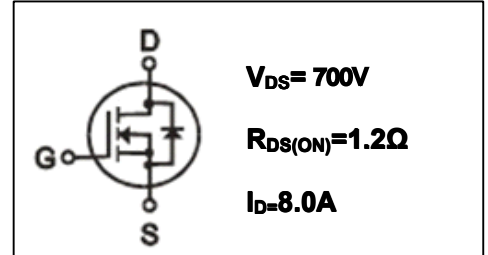


N-沟道功率 MOS 管/ N-CHANNEL POWER MOSFET
HU8N70
●特点：热阻低 开关速度快 输入阻抗高 符合RoHS规范
●FEATURES: ■LOW THERMAL RESISTANCE ■FAST SWITCHING ■HIGH INPUT RESISTANCE
■RoHS COMPLIANT
●应用：电子镇流器 电子变压器 开关电源
●APPLICATION: ■ELECTRONIC BALLAST ■ELECTRONIC TRANSFORMER ■SWITCH MODE POWER SUPPLY
●最大额定值 (TC=25°C)
●Absolute Maximum Ratings (Tc=25°C) TO-251/251T/252

参数 PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
漏-源电压 Drain-source Voltage	V_{DS}	700	V
栅-源电压 gate-source Voltage	V_{GS}	± 30	V
漏极电流 Continuous Drain Current TC=25°C	I_D	8.0	A
漏极电流 Continuous Drain Current TC=100°C	I_D	3.5	A
最大脉冲电流 Drain Current — Pulsed ①	I_{DM}	32	A
耗散功率 Power Dissipation	P_{tot}	50	W
最高结温 Junction Temperature	T_j	150	°C
存储温度 Storage Temperature	T_{STG}	-55-150	°C
单脉冲雪崩能量 Single Pulse Avalanche Energy ②	E_{AS}	230	mJ


●电特性 (Tc=25°C)
●Electronic Characteristics (Tc=25°C)

参数 PARAMETER	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	典型值 TYP	最大值 MAX	单位 UNIT
漏-源击穿电压 Drain-source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	700			V
击穿电压温度系数 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	$I_D = 250\mu A$, Referenced to 25°C		0.65		V/°C
栅极开启电压 Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.0		4.0	V
漏-源漏电流 Drain-source Leakage Current	I_{DSS}	$V_{DS} = 700V,$ $V_{GS} = 0V, T_j = 25^\circ C$			1	μA
		$V_{DS} = 520V,$ $V_{GS} = 0V, T_j = 125^\circ C$			10	μA
跨导 Forward Transconductance	g_{fs}	$V_{DS} = 40V, I_D = 4.0A$ ③		3.0		S

N-沟道功率 MOS 管/ N-CHANNEL POWER MOSFET

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参数 PARAMETER	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	典型值 TYP	最大值 MAX	单位 UNIT
栅极漏电流 Gate-body Leakage Current ($V_{DS} = 0$)	I_{GSS}	$V_{GS} = \pm 30V$			± 100	nA
漏-源导通电阻 Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 4.0A$ ③		0.93	1.2	Ω
输入电容 Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V$ $F = 1.0MHz$		1080		pF
关断延迟 Turn -Off Delay Time	$T_d(off)$	$V_{DD} = 300V, I_D = 8.0A$ $R_G = 25\Omega$ ③		81		ns
栅极电荷 Total Gate Charge	Q_g	$I_D = 8.0A, V_{DS} = 520V$ $V_{GS} = 10V$ ③		25.9		nC
栅源电荷 Gate-to-Source Charge	Q_{gs}			6		nC
栅漏电荷 Gate-to-Drain Charge	Q_{gd}			9.2		nC
二极管正向电流 Continuous Diode Forward Current	I_S				8.0	A
二极管正向压降 Diode Forward Voltage	V_{SD}	$T_j = 25^\circ C, I_S = 8.0A$ $V_{GS} = 0V$ ③			1.4	V
反向恢复时间 Reverse Recovery Time	t_{rr}	$T_j = 25^\circ C, I_f = 8.0A$ $di/dt = 100A/\mu s$ ③		365		ns
反向恢复电荷 Reverse Recovery Charge	Q_{rr}			3.4		μC

●热特性

● Thermal Characteristics

参数 PARAMETER	符号 SYMBOL	最大值 MAX	单位 UNIT
		TO-251/251T/252	
热阻结-壳 Thermal Resistance Junction-case	R_{thJC}	2.50	$^\circ C/W$
热阻结-环境 Thermal Resistance Junction-ambient	R_{thJA}	62.5	$^\circ C/W$

注释(Notes):

- ① 脉冲宽度：以最高节温为限制
Repetitive rating: Pulse width limited by maximum junction temperature
- ② 初始结温= $25^\circ C$, $V_{DD} = 50V$, $L = 10mH$, $R_G = 25\Omega$, $I_{AS} = 8.0A$
Starting $T_j = 25^\circ C$, $V_{DD} = 50V$, $L = 10mH$, $R_G = 25\Omega$, $I_{AS} = 8.0A$
- ③ 脉冲测试：脉冲宽度 $\leq 300\mu s$ ，占空比 $\leq 2\%$
Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

N-沟道功率 MOS 管/ N-CHANNEL POWER MOSFET

HU8N70

● 特性曲线

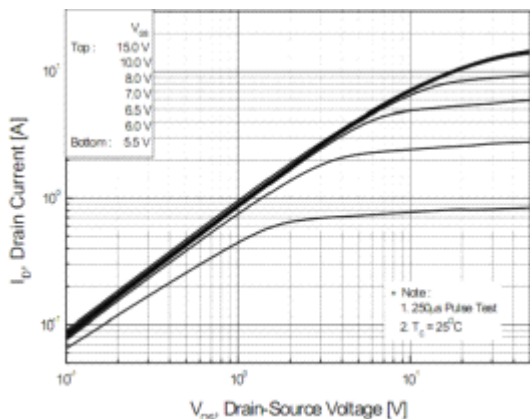


图1 输出特性曲线, Tc=25°C
Fig1 Typical Output Characteristics, Tc=25°C

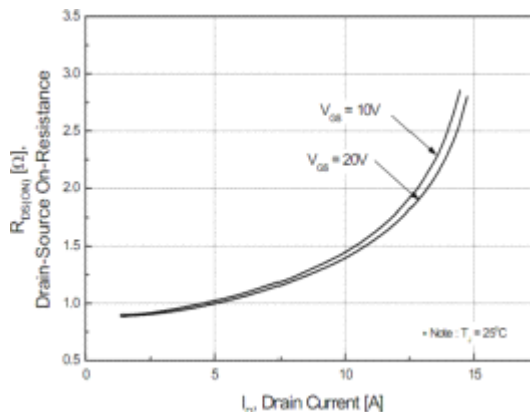


图2 导通电阻与漏极电流和栅极电压曲线
Fig2 On-Resistance Vs. Drain Current and Gate Voltage

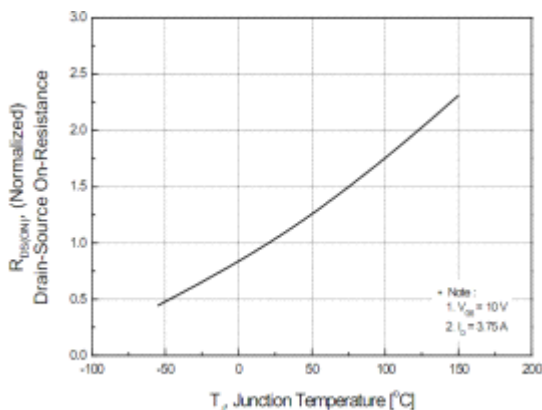


图3 导通电阻与温度曲线
Fig3 Normalized On-Resistance Vs. Temperature

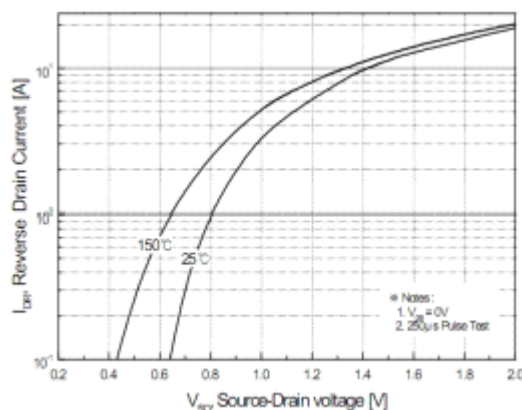


图4 二极管正向电压曲线
Fig4 Typical Source-Drain Diode Forward Voltage

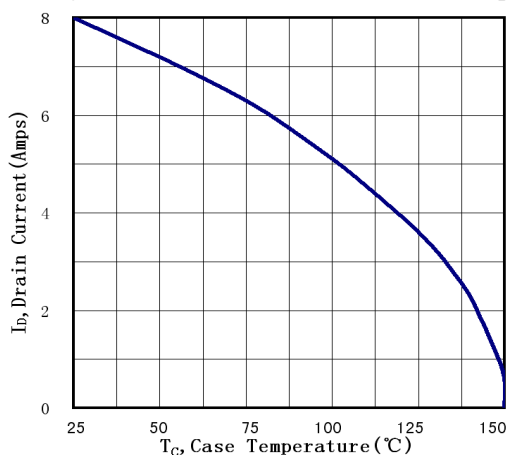


图5 最大漏极电流与壳温曲线
Fig5 Maximum Drain Current Vs. Case Temperature

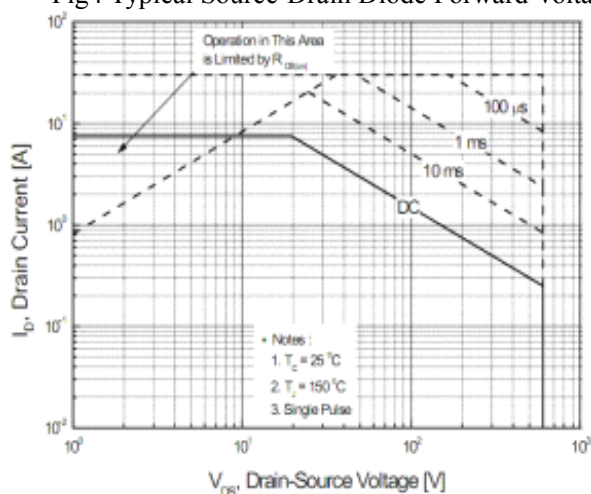


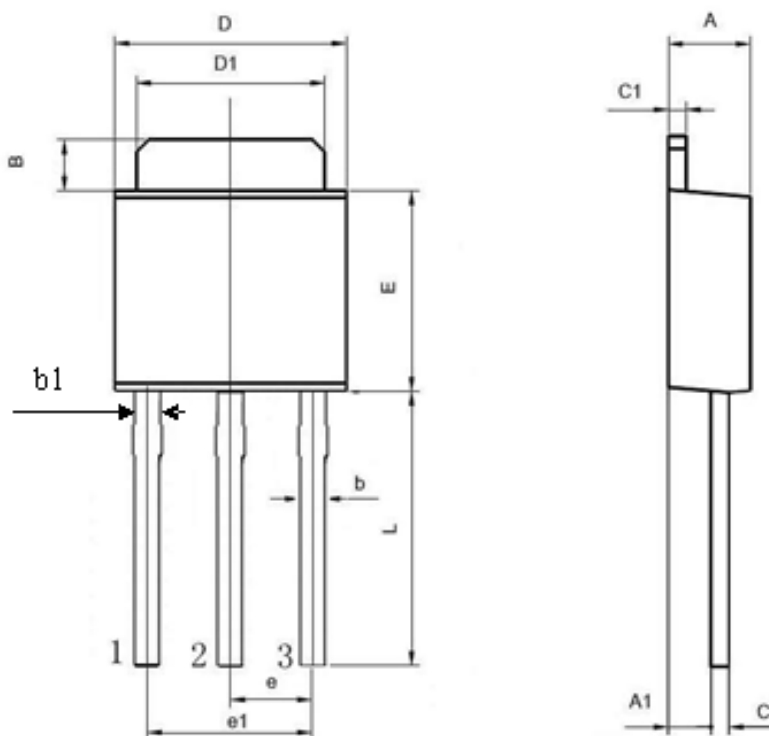
图6 最大安全工作区曲线
Fig6 Maximum Safe Operating Area

TO-251 封装机械尺寸 TO-251 (IPAK) MECHANICAL DATA

单位:毫米/UNIT: mm

符号/SYMBOL	最小值/min	典型值/nom	最大值/max
A	2.10		2.50
A ₁	0.95		1.30
B	0.80		1.25
b	0.50		0.80
b ₁	0.70		0.90
c	0.45		0.70
c ₁	0.45		0.70
D	6.35		6.80
D ₁	5.10		5.50
E	5.30		6.30
e		2.30	
L	7.00		9.20
R		0.30	

[S/L]

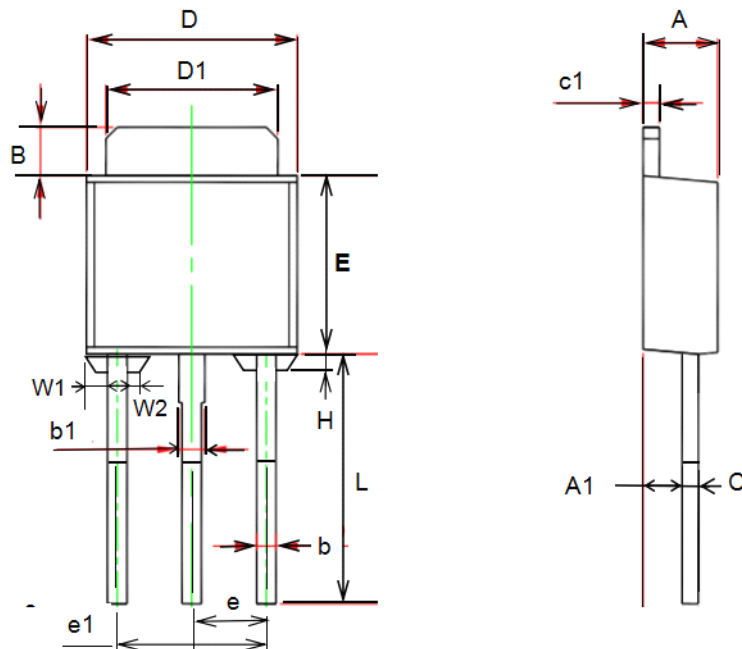


TO-251T 封装机械尺寸
TO-251T (IPAK) MECHANICAL DATA

单位:毫米/UNIT: mm

符号/SYMBOL	最小值/min	典型值/nom	最大值/max
A	2.10		2.50
A ₁	0.95		1.30
B	0.80		1.25
b	0.50		0.80
b ₁	0.70		0.90
c	0.45		0.70
c ₁	0.45		0.70
D	6.35		6.80
D ₁	5.10		5.50
E	5.30		6.30
e	2.25	2.30	2.35
L	7.00		9.20
H	0.35		0.45
W ₁	0.30		0.50
W ₂	0.20		0.40

[S/L]



TO-252 封装机械尺寸
TO-252 MECHANICAL DATA

单位:毫米/UNIT: mm

符号 SYMBOL	最小值 min	最大值 max	符号 SYMBOL	最小值 min	最大值 max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	-0.10	0.10			

